

## P-Channel Enhancement Mode MOSFET

### 1. Product Information

#### 1.1 Features

- Advanced trench cell design
- Low Thermal Resistance

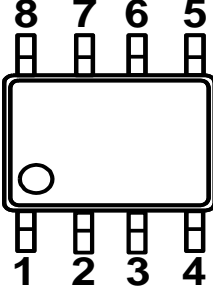
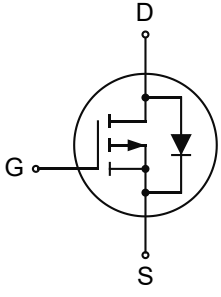
#### 1.2 Applications

- Motor drivers
- DC - DC Converter

#### 1.3 Quick reference

- $BV \geq -30\text{ V}$
- $R_{DS(ON)} \leq 18\text{ m}\Omega @ V_{GS}=-10\text{ V}$
- $P_{tot} \cong 20\text{ W}$
- $R_{DS(ON)} \leq 28\text{ m}\Omega @ V_{GS}=-4.5\text{ V}$
- $I_D \cong -10\text{ A}$

### 2. Pin Description

Pin	Description	Simplified Outline	Symbol
1,2,3	Source(S)	 <p style="text-align: center;">Top View SOP-8L</p>	
4	Gate(G)		
5,6,7,8	Drain(D)		

## 3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	Drain-Source Voltage	T <sub>C</sub> =25°C	-30	-	V
V <sub>GS</sub>	Gate-Source Voltage	T <sub>C</sub> =25°C	-	±20	V
I <sub>D</sub> *	Drain Current	T <sub>C</sub> =25°C, V <sub>GS</sub> =-10 V	-	-10	A
I <sub>DM</sub> <sup>*,**,***</sup>	Pulsed Source Current	T <sub>C</sub> =25°C, V <sub>GS</sub> =-10 V	-	-60	A
P <sub>tot</sub> *	Total Power Dissipation	T <sub>C</sub> =25°C	-	20	W
T <sub>stg</sub>	Storage Temperature		-55	150	°C
T <sub>J</sub>	Junction Temperature		-	150	°C
I <sub>S</sub>	Diode Forward Current	T <sub>C</sub> =25°C	-	-10	A
R <sub>θJC</sub> *	Thermal Resistance-Junction to Ambient		-	6	°C/W

Notes :

- \* Surface Mounted on 1 in<sup>2</sup> pad area, t ≤ 10 sec
- \*\* Pulse width ≤ 10 μs, duty cycle ≤ 1%
- \*\*\* Limited by bonding wire

## 4. Marking Information

Product Name	Marking
KJ15P03S	4435

## 5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ15P03S	SOP8			3000	

Note: KUIJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C)

## 6. Electrical Characteristics (T<sub>C</sub> = 25°C Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0 V, I <sub>D</sub> =-250 μA	-30	-	-	V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =-250 μA	-1.0	-	-2.0	V
I <sub>DSS</sub>	Zero Gate Voltage Source Current	V <sub>DS</sub> =-24 V, V <sub>GS</sub> =0 V	-	-	-1	μA
		T <sub>J</sub> =85°C	-	-	-30	μA
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> =±20 V, V <sub>DS</sub> =0 V	-	-	±100	nA
R <sub>DS(ON)</sub> <sup>a</sup>	Drain-Source On-State Resistance	V <sub>GS</sub> =-10 V, I <sub>D</sub> =-8 A	-	14.5	18	mΩ
		V <sub>GS</sub> =-4.5 V, I <sub>D</sub> =-5 A	-	24	28	mΩ
<b>Diode Characteristics</b>						
V <sub>SD</sub> <sup>a</sup>	Diode Forward Voltage	I <sub>SD</sub> =-8 A, V <sub>GS</sub> =0 V	-	-	-1.3	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>SD</sub> =-8 A, dI <sub>SD</sub> /dt=100 A/μs	-	8.3	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	0.6	-	nC
<b>Dynamic Characteristics<sup>b</sup></b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0 V, V <sub>DS</sub> =-15 V Frequency=1 MHz	-	1811	-	pF
C <sub>oss</sub>	Output Capacitance		-	172	-	
C <sub>rss</sub>	Reverse Transfer Capacitance		-	134	-	
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =-15 V, V <sub>GEN</sub> =-10 V, R <sub>G</sub> =4.5 Ω, R <sub>L</sub> =0.75 Ω, I <sub>D</sub> =-8 A	-	18	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	86	-	
t <sub>d(off)</sub>	Turn-off Delay Time		-	231	-	
t <sub>f</sub>	Turn-off Fall Time		-	127	-	
<b>Gate Charge Characteristics<sup>b</sup></b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =-10 V, V <sub>DS</sub> =-15 V, I <sub>DS</sub> =-8 A	-	31	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	8.6	-	
Q <sub>gd</sub>	Gate-Drain Charge		-	4.8	-	

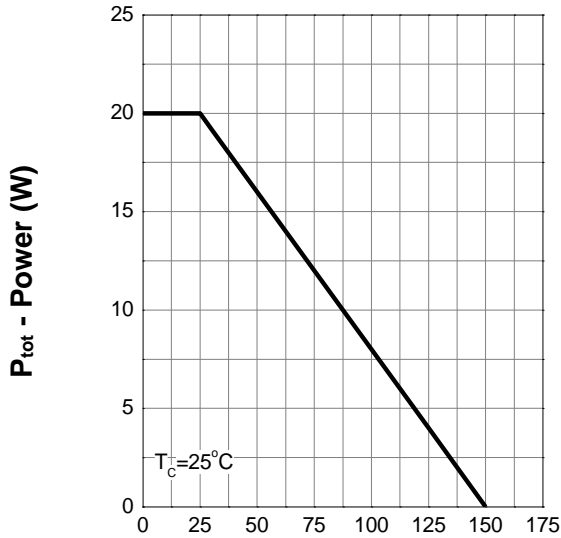
Notes :

a : Pulse test ; pulse width ≤ 300 μs, duty cycle ≤ 2%

b : Guaranteed by design, not subject to production testing

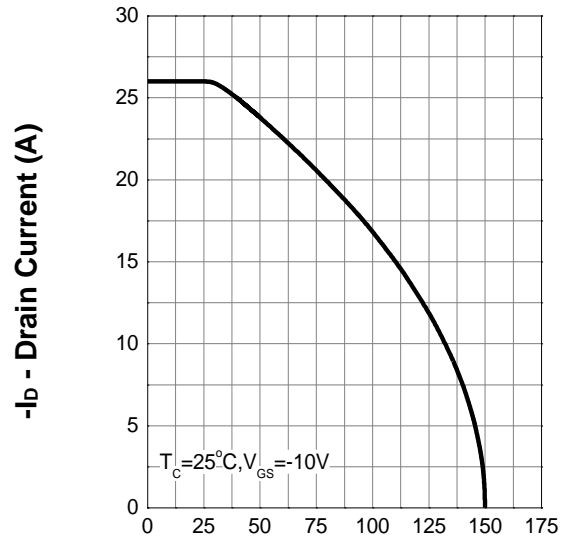
## 7. Typical Characteristics

### Power Capability



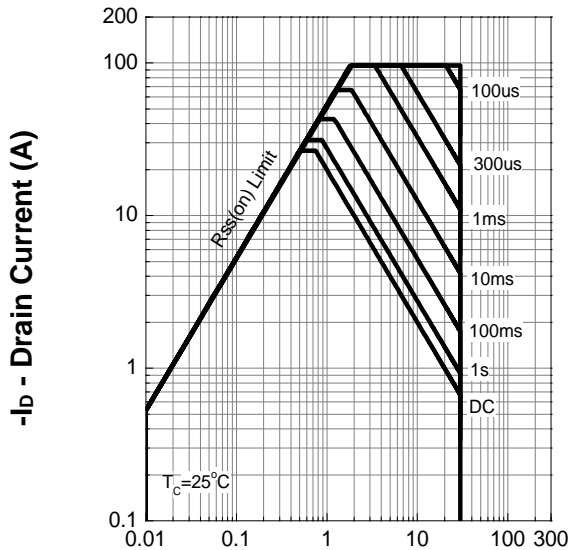
T<sub>j</sub> - Junction Temperature (°C)

### Current Capability



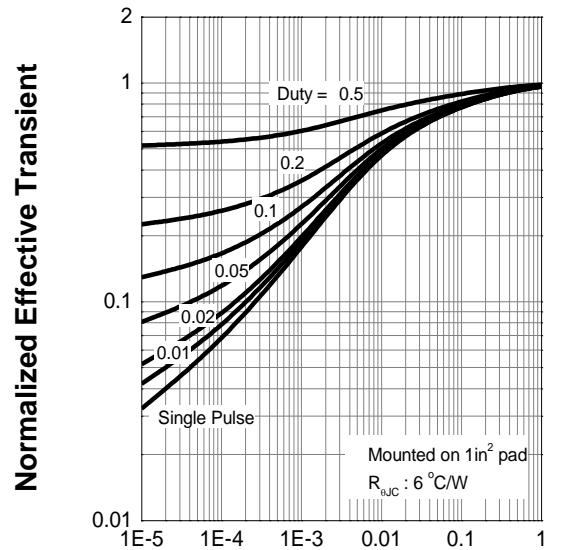
T<sub>j</sub> - Junction Temperature (°C)

### Safe Operation Area



-V<sub>DS</sub> - Drain-Source Voltage (V)

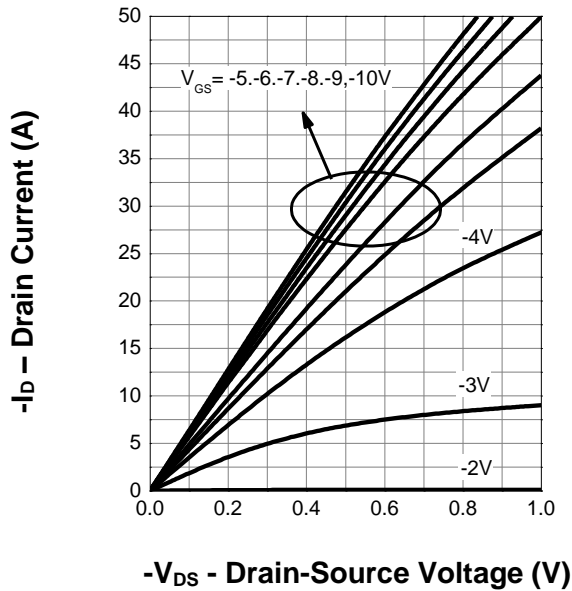
### Thermal Transient Impedance



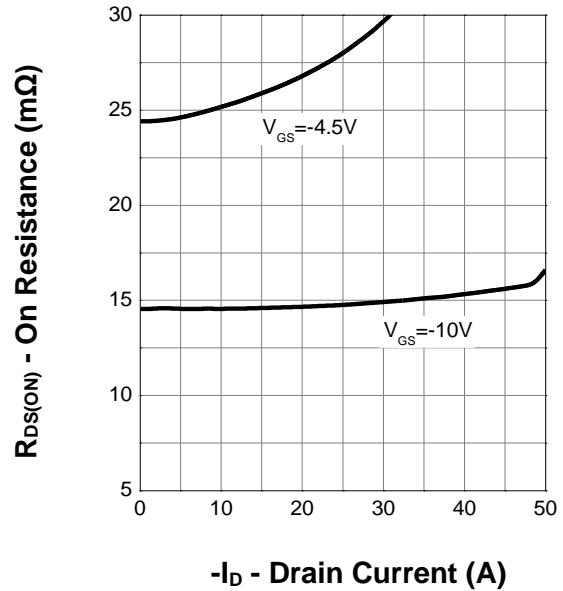
Square Wave Pulse Duration (sec)

## 7. Typical Characteristics (cont.)

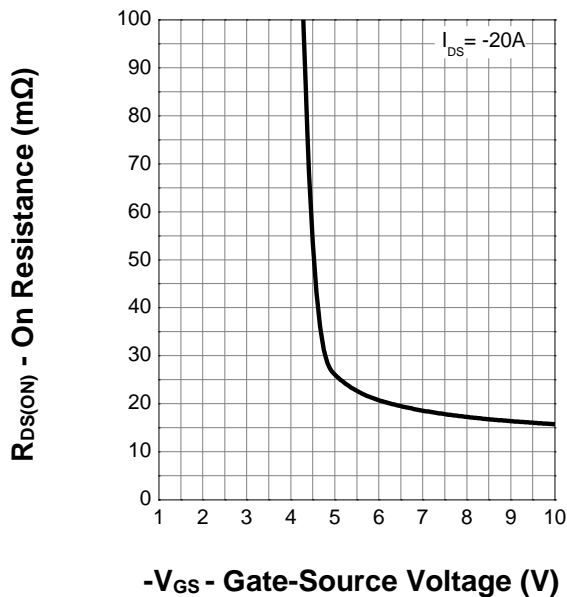
**Output Characteristics**



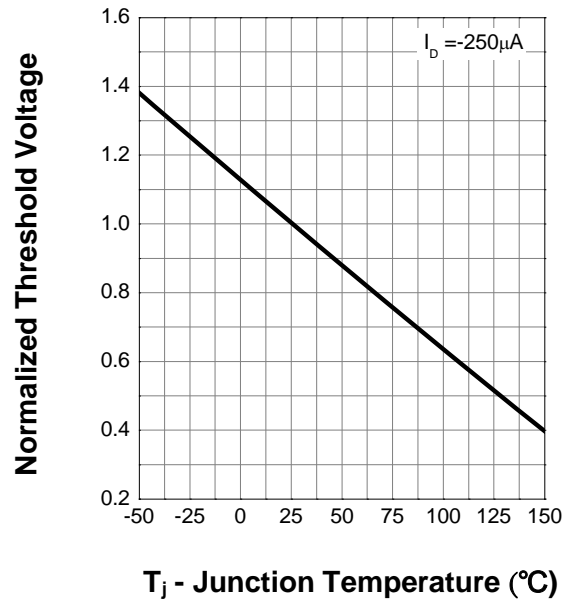
**Drain-Source On Resistance**



**Transfer Characteristics**

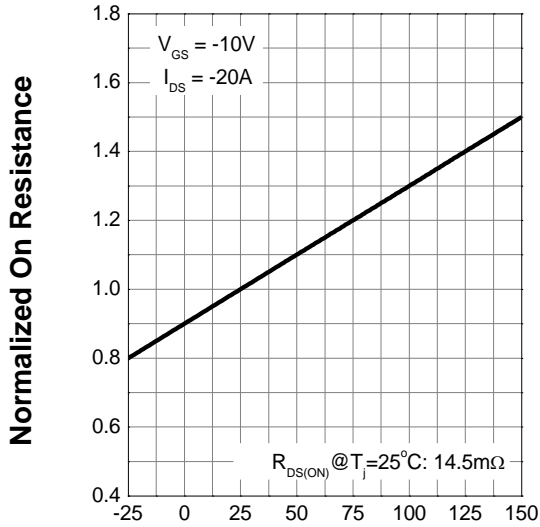


**Gate Threshold Voltage**



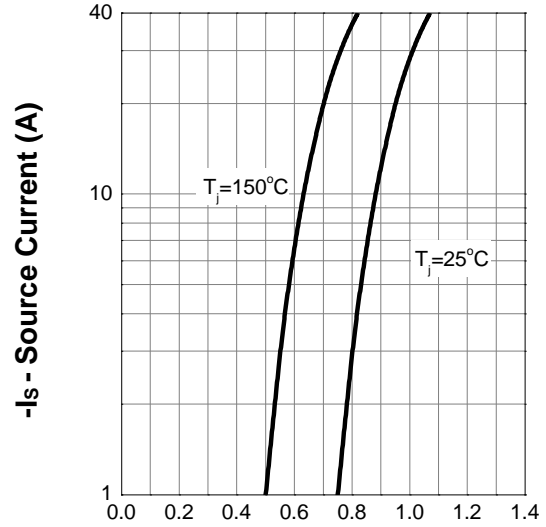
## 7. Typical Characteristics (cont.)

### Drain-Source On Resistance



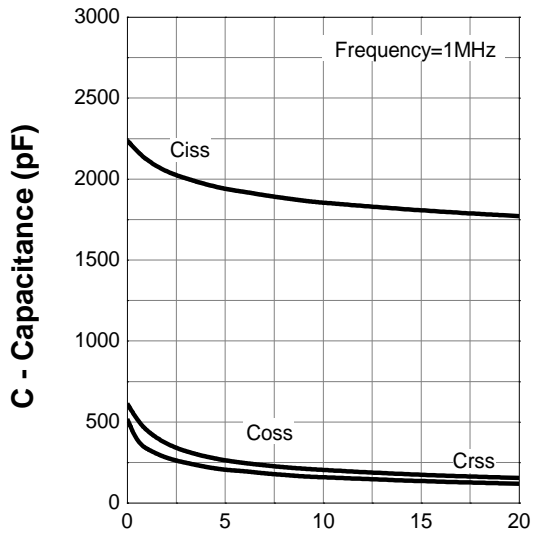
$T_j$  - Junction Temperature ( $^{\circ}\text{C}$ )

### Body Diode Characteristics



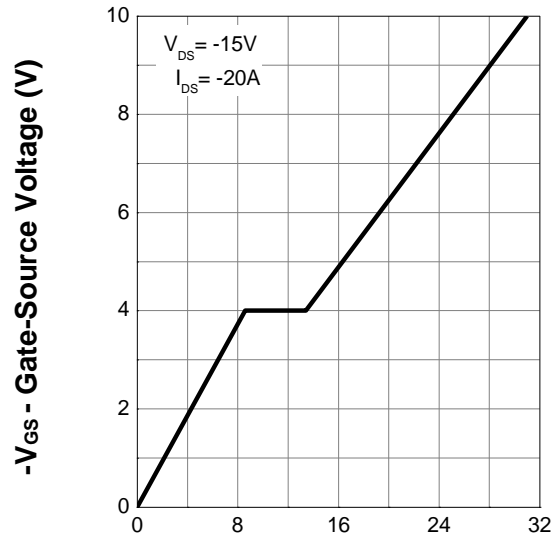
$-V_{SD}$  - Source-Drain Voltage (V)

### Capacitance



$-V_{DS}$  - Drain-Source Voltage (V)

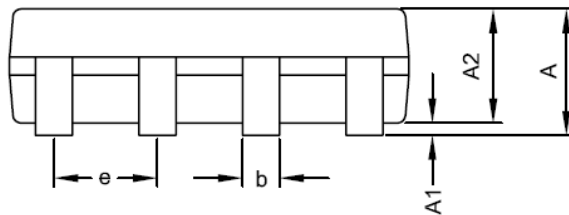
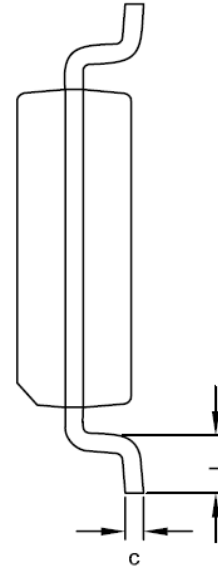
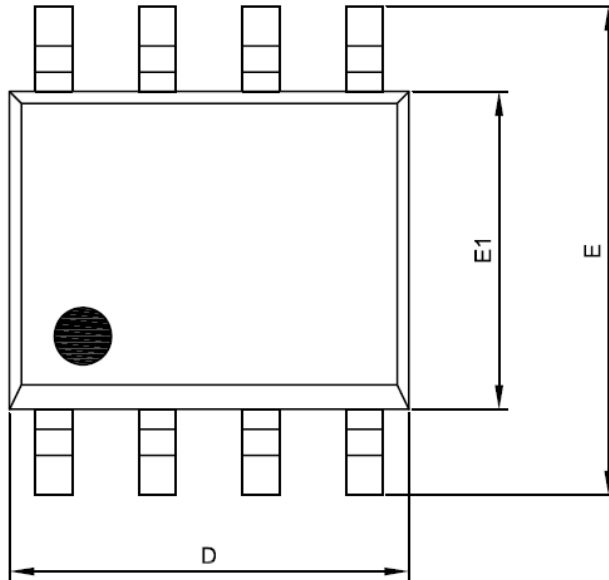
### Gate Charge



$Q_G$  - Gate Charge (nC)

## 8. Package Dimensions

### SOP8 Package



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	1.35	1.75
A1	0.00	0.25
A2	1.15	1.50
D	4.80	5.00
E	5.80	6.20
E1	3.80	4.00
c	0.19	0.27
b	0.33	0.53
e	1.27 BSC	
L	0.40	1.27

#### Notes :

1. Jedec outline: MS-012AA
2. Dimensions "D" does not include mold flash, protrusions and gate burrs shall not exceed .15 mm (.006 in) per side.
3. Dimensions "E1" does not include inter-lead flash, or protrusions. Inter-lead flash and protrusions shall not exceed .25 mm (.010 in) per side.